

# Philips Components

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# 10107 Gate

Triple 2-Input Exclusive-OR/Exclusive-NOR Gate

## FEATURES

- Typical propagation delay: 2.8ns
- Typical supply current ( $-I_{EE}$ ): 22mA

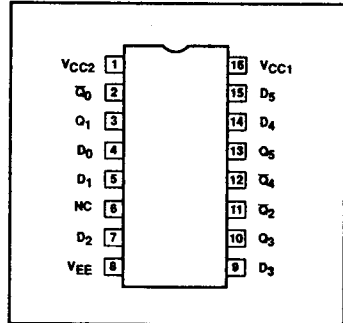
## DESCRIPTION

The 10107 is a three gate array designed to provide the positive Exclusive-OR and NOR functions. All unused inputs can be left open due to pull-down resistors which avoid the need for a supply voltage.

## ORDERING INFORMATION

DESCRIPTION	ORDER CODE
16-Pin Plastic DIP	10107N
16-Pin Ceramic DIP	10107F
16-Pin SO	10107D

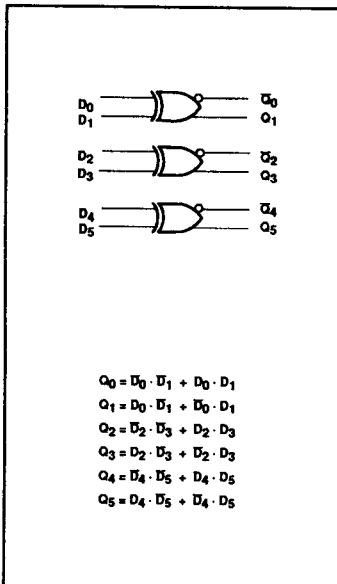
## PIN CONFIGURATION



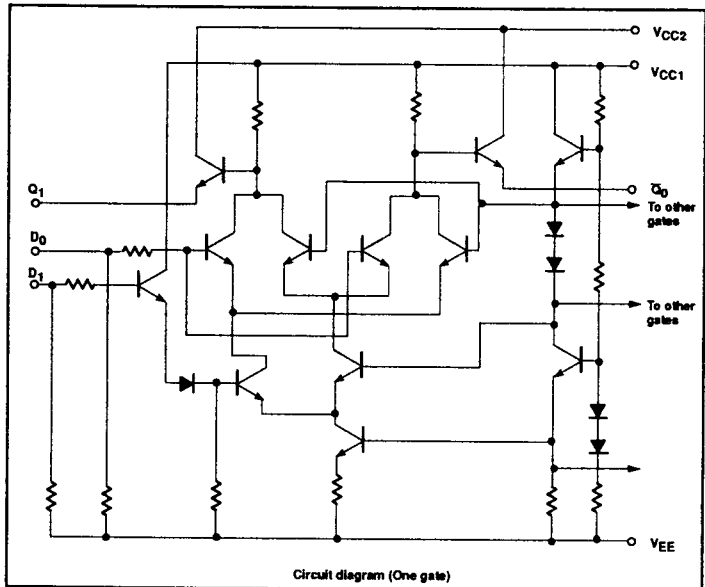
## PIN DESCRIPTION

PINS	DESCRIPTION
D <sub>0</sub> - D <sub>5</sub>	Data Inputs
Q <sub>1</sub> , Q <sub>3</sub> , Q <sub>5</sub>	Data Outputs (OR)
Q <sub>0</sub> , Q <sub>2</sub> , Q <sub>4</sub>	Data Outputs (NOR)

## LOGIC DIAGRAM



## SIMPLIFIED SCHEMATIC



## Gate

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## ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	LIMITS	UNIT	
$V_{EE}$	Supply voltage	-8.0	V	
$V_{IN}$	Input voltage ( $V_{IN}$ should never be more negative than $V_{EE}$ )	0 to $V_{EE}$	V	
$I_O$	Output source current (continuous)	-50	mA	
$T_S$	Storage temperature range	-55 to +150	°C	
$T_J$	Maximum junction temperature	Ceramic Package	+165	°C
		Plastic Package	+150	°C

## NOTE:

Operation beyond the limits set forth in this table may impair the useful life of the device. Unless otherwise noted, these limits are specified over the operating ambient temperature range.

## DC OPERATING CONDITIONS

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN.	NOM.	MAX.	
$V_{CC1}, V_{CC2}$	Circuit ground		0	0	0	V
$V_{EE}$	Supply voltage (negative)			-5.2		V
$V_{IH}$	High level input voltage	$T_A = -30^\circ\text{C}$			-890	mV
		$T_A = +25^\circ\text{C}$			-810	mV
		$T_A = +85^\circ\text{C}$			-700	mV
$V_{IHT}$	High level input threshold voltage	$T_A = -30^\circ\text{C}$	-1205			mV
		$T_A = +25^\circ\text{C}$	-1105			mV
		$T_A = +85^\circ\text{C}$	-1035			mV
$V_{ILT}$	Low level input threshold voltage	$T_A = -30^\circ\text{C}$			-1500	mV
		$T_A = +25^\circ\text{C}$			-1475	mV
		$T_A = +85^\circ\text{C}$			-1440	mV
$V_{IL}$	Low level input voltage	$T_A = -30^\circ\text{C}$	-1890			mV
		$T_A = +25^\circ\text{C}$	-1850			mV
		$T_A = +85^\circ\text{C}$	-1825			mV
$T_A$	Operating ambient temperature range		-30	+25	+85	°C

## NOTE:

When operating at other than the specified  $V_{EE}$  voltage (-5.2V), the DC and AC Electrical Characteristics will vary slightly from specified values.

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**DC ELECTRICAL CHARACTERISTICS**  $V_{CC1} = V_{CC2} = \text{ground}$ ,  $V_{EE} = -5.2V \pm 0.010V$ ,  $T_A = -30^\circ\text{C}$  to  $+85^\circ\text{C}$  output loading 50Ω to  $-2.0V \pm 0.010V$  unless otherwise specified<sup>1,3</sup>

SYMBOL	PARAMETER		TEST CONDITIONS <sup>2</sup>		LIMITS			UNIT
					MIN.	TYP.	MAX.	
$V_{OH}$	High level output voltage		$T_A = -30^\circ\text{C}$	For $Q_n$ outputs, apply $V_{ILMIN}$ to all inputs. For $Q_n$ outputs, apply $V_{IHMAX}$ to each input (D <sub>1</sub> , D <sub>2</sub> , D <sub>5</sub> ), one at a time, w/ $V_{ILMIN}$ applied to all other inputs. For $Q_n$ outputs apply $V_{IHMAX}$ to each input (D <sub>0</sub> , D <sub>3</sub> , D <sub>4</sub> ), one at a time, w/ $V_{ILMIN}$ applied to all inputs. For $Q_n$ outputs, apply $V_{IHMAX}$ to all inputs.	-1060		-890	mV
			$T_A = +25^\circ\text{C}$		-960		-810	mV
			$T_A = +85^\circ\text{C}$		-890		-700	mV
$V_{OHT}$	High level output threshold voltage		$T_A = -30^\circ\text{C}$	For $Q_n$ outputs, apply $V_{IHT}$ to one gate input with $V_{ILMIN}$ applied to the other gate input. For $Q_n$ outputs, apply $V_{IHT}$ to one gate input with $V_{ILMAX}$ applied to the other gate input.	-1080			mV
			$T_A = +25^\circ\text{C}$		-980			mV
			$T_A = +85^\circ\text{C}$		-910			mV
$V_{OLT}$	Low level output threshold voltage		$T_A = -30^\circ\text{C}$	For $Q_n$ outputs, apply $V_{ILT}$ to one gate input with $V_{ILMIN}$ applied to the other gate input. For $Q_n$ outputs, apply $V_{IHT}$ to one gate input with $V_{ILMIN}$ applied to the other gate input.			-1655	mV
			$T_A = +25^\circ\text{C}$				-1630	mV
			$T_A = +85^\circ\text{C}$				-1595	mV
$V_{OL}$	Low level output voltage		$T_A = -30^\circ\text{C}$	For $Q_n$ outputs, apply $V_{ILMIN}$ to all inputs. For $Q_n$ outputs, apply $V_{IHMAX}$ to each input (D <sub>1</sub> , D <sub>2</sub> , D <sub>5</sub> ), one at a time, w/ $V_{ILMIN}$ applied to all other inputs. For $Q_n$ outputs apply $V_{IHMAX}$ to each input (D <sub>0</sub> , D <sub>3</sub> , D <sub>4</sub> ), one at a time, w/ $V_{ILMIN}$ applied to all inputs. For $Q_n$ outputs, apply $V_{IHMAX}$ to all inputs.	-1890		-1675	mV
			$T_A = +25^\circ\text{C}$		-1850		-1650	mV
			$T_A = +85^\circ\text{C}$		-1825		-1615	mV
$I_{IH}$	High level input current	D <sub>0</sub> , D <sub>3</sub> , D <sub>4</sub> inputs	$T_A = -30^\circ\text{C}$	Apply $V_{IHMAX}$ to each input under test, one at a time, with $V_{ILMIN}$ applied to all other inputs.			425	μA
			$T_A = +25^\circ\text{C}$				265	μA
			$T_A = +85^\circ\text{C}$				265	μA
		D <sub>1</sub> , D <sub>2</sub> , D <sub>5</sub> inputs	$T_A = -30^\circ\text{C}$	Apply $V_{IHMAX}$ to each input under test, one at a time, with $V_{ILMIN}$ applied to all other inputs.			350	μA
			$T_A = +25^\circ\text{C}$				220	μA
			$T_A = +85^\circ\text{C}$				220	μA
$I_{IL}$	Low level input current		$T_A = -30^\circ\text{C}$	Apply $V_{ILMIN}$ to each input under test, one at a time, with $V_{IHMAX}$ applied to all other inputs.	0.5			μA
			$T_A = +25^\circ\text{C}$		0.5			μA
			$T_A = +85^\circ\text{C}$		0.3			μA
- $I_{EE}$	$V_{EE}$ supply current		$T_A = -30^\circ\text{C}$	Apply $V_{IHMAX}$ to D <sub>1</sub> , D <sub>2</sub> , D <sub>5</sub>			31	mA
			$T_A = +25^\circ\text{C}$				28	mA
			$T_A = +85^\circ\text{C}$				31	mA
$\frac{\Delta V_{OH}}{\Delta V_{EE}}$	High level output voltage compensation		$T_A = +25^\circ\text{C}$			0.016		V/V
$\frac{\Delta V_{OL}}{\Delta V_{EE}}$	Low level output voltage compensation					0.250		V/V
$\frac{\Delta V_{BB}}{\Delta V_{EE}}$	Reference bias voltage compensation					0.148		V/V

## NOTES:

- The specified limits represent the worst case values for the parameter. Since these worst case values normally occur at the supply voltage and temperature extremes, additional noise immunity can be achieved by decreasing the allowable operating condition ranges.
- Conditions for testing shown in the tables are not necessarily worst case. For worst case testing guidelines, refer to DC Testing, Chapter 1, Section 3.
- The specified limits shown in the DC Electrical Characteristics table can be met only after thermal equilibrium has been established. Thermal equilibrium is established by applying power for at least 2 minutes, while maintaining transverse airflow of 2.5 meters/sec (500 linear feet/min) over the device, mounted either in a test socket or on a printed circuit board. Test voltage values are given in the DC Operating Conditions table.

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**AC ELECTRICAL CHARACTERISTICS**  $V_{CC1} = V_{CC2} = \text{ground}, V_{EE} = -5.2V \pm 0.010V$

SYMBOL	PARAMETER	TEST CONDITION	LIMITS							UNIT
			$T_A = -30^\circ\text{C}$		$T_A = +25^\circ\text{C}$			$T_A = +85^\circ\text{C}$		
			MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.	
$t_{PLH}$ $t_{PHL}$	Propagation delay $D_n$ to $Q_n, \bar{Q}_n$	Waveform 1	1.10 1.10	3.80 3.80	1.10 1.10	2.80 2.80	3.70 3.70	1.10 1.10	4.00 4.00	ns ns
$t_{TLH}$ $t_{THL}$	Transition time 20% to 80%, 80% to 20%	Waveform 1	1.10 1.10	3.50 3.50	1.10 1.10	2.50 2.50	3.50 3.50	1.10 1.10	3.80 3.80	ns ns

**NOTE:**

For AC test setup information, see AC Testing, Chapter 2, Section 3.

**AC WAVEFORMS**

